

AMENDMENTS TO THE CLAIMS

This following Listing of Claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-5. (Canceled)

6. (Currently amended) ~~The light emitting apparatus according to 1,~~

A light emitting apparatus comprising:

a light emitting device disposed on a supporting body; and

a coating layer comprising a fluorescent substance and covering at least a surface of said light emitting device, said fluorescent substance absorbs at least a portion of light emitted by said light emitting device and emits light of a different wavelength;

wherein said coating layer comprises an oxide including at least one element selected from the group consisting of Si, Al, Ga, Ti, Ge, P, B, Zr, Y, Sn, Pb and alkali earth metals, and a hydroxide including at least one element selected from the group consisting of Si, Al, Ga, Ti, Ge, P, B, Zr, Y, Sn, Pb and alkali earth metals

wherein said coating layer covers the surface of said supporting body and the entire surface of said light emitting device, and the thickness of said coating layer on a top surface, a side face and a corner of said light emitting device and the thickness of said coating layer on a surface of said supporting body are substantially the same.

7. (Currently amended) ~~The light emitting apparatus according to 1,~~

A light emitting apparatus comprising:

a light emitting device disposed on a supporting body; and

a coating layer comprising a fluorescent substance and covering at least a surface of said light emitting device, said fluorescent substance absorbs at least a portion of light emitted by said light emitting device and emits light of a different wavelength;

wherein said coating layer comprises an oxide including at least one element selected from the group consisting of Si, Al, Ga, Ti, Ge, P, B, Zr, Y, Sn, Pb and alkali earth metals, and a hydroxide including at least one element selected from the group consisting of Si, Al, Ga, Ti, Ge, P, B, Zr, Y, Sn, Pb and alkali earth metals

wherein said coating layer comprises at least two layers, each layer having a refractive index that is smaller than that of a nitride semiconductor of said light emitting device, and the refractive index of each layer decreases gradually with the distance from said light emitting device.

8. (Currently amended) ~~The light emitting apparatus according to 1,~~

A light emitting apparatus comprising:

a light emitting device disposed on a supporting body; and

a coating layer comprising a fluorescent substance and covering at least a surface of said light emitting device, said fluorescent substance absorbs at least a portion of light emitted by said light emitting device and emits light of a different wavelength;

wherein said coating layer comprises an oxide including at least one element selected from the group consisting of Si, Al, Ga, Ti, Ge, P, B, Zr, Y, Sn, Pb and alkali earth metals, and a hydroxide including at least one element selected from the group consisting of Si, Al, Ga, Ti, Ge, P, B, Zr, Y, Sn, Pb and alkali earth metals

wherein said light emitting device is disposed so as to oppose the top surface of said supporting body via an adhesive layer, while the adhesive layer contains the same material as that of said coating layer.

9. (Previously Presented) The light emitting apparatus according to 8,

wherein said adhesive layer contains particles of an oxide and a hydroxide.

10. (Previously Presented) The light emitting apparatus according to 8,

wherein said adhesive layer extends over a side face of said light emitting device.

11. (Currently amended) ~~The light emitting apparatus according to 1,~~

A light emitting apparatus comprising:

a light emitting device disposed on a supporting body; and
a coating layer comprising a fluorescent substance and covering at least a surface of said light emitting device, said fluorescent substance absorbs at least a portion of light emitted by said light emitting device and emits light of a different wavelength;

wherein said coating layer comprises an oxide including at least one element selected from the group consisting of Si, Al, Ga, Ti, Ge, P, B, Zr, Y, Sn, Pb and alkali earth metals, and a hydroxide including at least one element selected from the group consisting of Si, Al, Ga, Ti, Ge, P, B, Zr, Y, Sn, Pb and alkali earth metals

wherein said light emitting device has an emission peak at a wavelength from 250 nm to 530 nm, and an emission wavelength of said fluorescent substance is longer than a wavelength of the main emission peak of said light emitting device.

12. (Currently amended) ~~The light emitting apparatus according to 1,~~

A light emitting apparatus comprising:

a light emitting device disposed on a supporting body; and
a coating layer comprising a fluorescent substance and covering at least a surface of said light emitting device, said fluorescent substance absorbs at least a portion of light emitted by said light emitting device and emits light of a different wavelength;

wherein said coating layer comprises an oxide including at least one element selected from the group consisting of Si, Al, Ga, Ti, Ge, P, B, Zr, Y, Sn, Pb and alkali earth metals, and a hydroxide including at least one element selected from the group consisting of Si, Al, Ga, Ti, Ge, P, B, Zr, Y, Sn, Pb and alkali earth metals

wherein said fluorescent substance is yttrium aluminum garnet-containing fluorescent substance that includes: Y; Al; at least one element selected from the group consisting of Lu, Sc, La, Gd, Tb, Eu and Sm; and at least one element selected from the group consisting of Ga and In,

and said fluorescent substance is activated with a rare earth element.

13. (Currently amended) ~~The light emitting apparatus according to 1,~~

A light emitting apparatus comprising:

a light emitting device disposed on a supporting body; and

a coating layer comprising a fluorescent substance and covering at least a surface of said light emitting device, said fluorescent substance absorbs at least a portion of light emitted by said light emitting device and emits light of a different wavelength;

wherein said coating layer comprises an oxide including at least one element selected from the group consisting of Si, Al, Ga, Ti, Ge, P, B, Zr, Y, Sn, Pb and alkali earth metals, and a hydroxide including at least one element selected from the group consisting of Si, Al, Ga, Ti, Ge, P, B, Zr, Y, Sn, Pb and alkali earth metals

wherein said fluorescent substance includes: N; at least one element selected from the group consisting of Be, Mg, Ca, Sr, Ba and Zn; at least one element selected from the group consisting of C, Si, Ge, Sn, Ti, Zr and Hf; and a nitride-containing fluorescent substance activated with a rare earth element.

14-17. (Canceled).

18. (Previously Presented) A light emitting apparatus comprising: a supporting body; an adhesive layer, and a light emitting device comprising a gallium nitride-containing compound semiconductor layer, said light emitting device being disposed on said supporting substrate via the adhesive layer;

wherein said adhesive layer comprises an oxide containing at least one element selected from the group consisting of Si, Al, Ga, Ti, Ge, P, B, Zr, Y, Sn, Pb and alkali earth metals, and a hydroxide containing at least one element selected from the group consisting of Si, Al, Ga, Ti, Ge, P, B, Zr, Y, Sn, Pb and alkali earth metals,

wherein said adhesive layer extends over a side face of the light emitting device.

19. (Previously Presented) A light emitting apparatus comprising: a supporting body; an adhesive layer, and a light emitting device comprising a gallium nitride-containing compound semiconductor layer, said light emitting device being disposed on said supporting substrate via the adhesive layer;

wherein said adhesive layer comprises an oxide containing at least one element selected from the group consisting of Si, Al, Ga, Ti, Ge, P, B, Zr, Y, Sn, Pb and alkali earth

metals, and a hydroxide containing at least one element selected from the group consisting of Si, Al, Ga, Ti, Ge, P, B, Zr, Y, Sn, Pb and alkali earth metals,

wherein said light emitting device has a main emission peak at a wavelength in a range from 250 nm to 530 nm.

20. (Previously Presented) A light emitting apparatus comprising: a supporting body; an adhesive layer, and a light emitting device comprising a gallium nitride-containing compound semiconductor layer, said light emitting device being disposed on said supporting substrate via the adhesive layer;

wherein said adhesive layer comprises an oxide containing at least one element selected from the group consisting of Si, Al, Ga, Ti, Ge, P, B, Zr, Y, Sn, Pb and alkali earth metals, and a hydroxide containing at least one element selected from the group consisting of Si, Al, Ga, Ti, Ge, P, B, Zr, Y, Sn, Pb and alkali earth metals,

wherein the adhesive layer comprises a filler having a heat conductivity higher than that of said oxide.

21. (Currently amended) ~~The light emitting apparatus according to 1 or 15,~~

A light emitting apparatus comprising:

a light emitting device disposed on a supporting body; and

a coating layer comprising a fluorescent substance and covering at least a surface of said light emitting device, said fluorescent substance absorbs at least a portion of light emitted by said light emitting device and emits light of a different wavelength;

wherein said coating layer comprises an oxide including at least one element selected from the group consisting of Si, Al, Ga, Ti, Ge, P, B, Zr, Y, Sn, Pb and alkali earth metals, and a hydroxide including at least one element selected from the group consisting of Si, Al, Ga, Ti, Ge, P, B, Zr, Y, Sn, Pb and alkali earth metals

wherein said light emitting device includes:

a support substrate;

a junction layer that is formed on one principal surface of the support substrate, said junction layer having a eutectic layer; and

stacked layers comprising a p-type nitride semiconductor layer of single-layer or multi-layer structure formed on the junction layer, an active layer formed on the p-type nitride semiconductor layer, and an n-type nitride semiconductor layer of single-layer or multi-layer structure formed on the active layer.

22. (Previously Presented) The light emitting apparatus according to 21,
wherein at least part of a surface of the stacked layers has a concave-convex shape.

23-41. (Canceled)